



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



**COMPLEMENTARY NPN / PNP SMALL SIGNAL SURFACE MOUNT TRANSISTOR**
**Features**

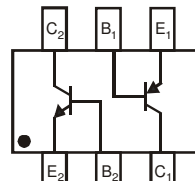
- Complementary Pair One 4124-Type NPN  
One 4126-Type PNP
- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- Ultra-Small Surface Mount Package
- Lead Free/RoHS Compliant (Note 3)**
- "Green" Device (Note 4 and 5)**

**Mechanical Data**

- Case: SOT-363
- Case Material: Molded Plastic, "Green" Molding Compound, Note 5. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating) Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.006 grams (approximate)



Top View



Device Schematic

 E1, B1, C1 = PNP4126 Section  
 E2, B2, C2 = NPN4124 Section

**Maximum Ratings, NPN 4124 Section** @<sub>T<sub>A</sub></sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	30	V
Collector-Emitter Voltage	V <sub>CEO</sub>	25	V
Emitter-Base Voltage	V <sub>EBO</sub>	5.0	V
Collector Current – Continuous (Note 1)	I <sub>C</sub>	200	mA

**Maximum Ratings, PNP 4126 Section** @<sub>T<sub>A</sub></sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-25	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-25	V
Emitter-Base Voltage	V <sub>EBO</sub>	-4	V
Collector Current - Continuous (Note 1)	I <sub>C</sub>	-200	mA

**Thermal Characteristics – Total Device**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 1, 2)	P <sub>D</sub>	200	mW
Thermal Resistance, Junction to Ambient (Note 1)	R <sub>θJA</sub>	625	°C/W

- Notes:
- Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
  - Maximum combined dissipation.
  - No purposefully added lead.
  - Diodes Inc.'s "Green" policy can be found on our website at [http://www.diodes.com/products/lead\\_free/index.php](http://www.diodes.com/products/lead_free/index.php).
  - Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

**Electrical Characteristics, NPN 4124 Section** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 6)</b>					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	30	—	V	$I_C = 10\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	25	—	V	$I_C = 1.0\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5.0	—	V	$I_E = 10\mu\text{A}, I_C = 0$
Collector Cutoff Current	$I_{CBO}$	—	50	nA	$V_{CB} = 20\text{V}, I_E = 0\text{V}$
Emitter Cutoff Current	$I_{EBO}$	—	50	nA	$V_{EB} = 3.0\text{V}, I_C = 0\text{V}$
<b>ON CHARACTERISTICS (Note 6)</b>					
DC Current Gain	$h_{FE}$	120 60	360 —	—	$I_C = 2.0\text{mA}, V_{CE} = 1.0\text{V}$ $I_C = 50\text{mA}, V_{CE} = 1.0\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	0.30	V	$I_C = 50\text{mA}, I_B = 5.0\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	0.95	V	$I_C = 50\text{mA}, I_B = 5.0\text{mA}$
<b>SMALL SIGNAL CHARACTERISTICS</b>					
Output Capacitance	$C_{obo}$	—	4.0	pF	$V_{CB} = 5.0\text{V}, f = 1.0\text{MHz}, I_E = 0$
Input Capacitance	$C_{ibo}$	—	8.0	pF	$V_{EB} = 0.5\text{V}, f = 1.0\text{MHz}, I_C = 0$
Small Signal Current Gain	$h_{fe}$	120	480	—	$V_{CE} = 1.0\text{V}, I_C = 2.0\text{mA},$ $f = 1.0\text{kHz}$
Current Gain-Bandwidth Product	$f_T$	300	—	MHz	$V_{CE} = 20\text{V}, I_C = 10\text{mA},$ $f = 100\text{MHz}$
Noise Figure	NF	—	5.0	dB	$V_{CE} = 5.0\text{V}, I_C = 100\mu\text{A},$ $R_S = 1.0\text{k}\Omega, f = 1.0\text{kHz}$

**Electrical Characteristics, PNP 4126 Section** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 6)</b>					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-25	—	V	$I_C = -10\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-25	—	V	$I_C = -1.0\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-4.0	—	V	$I_E = -10\mu\text{A}, I_C = 0$
Collector Cutoff Current	$I_{CBO}$	—	-50	nA	$V_{CB} = -20\text{V}, I_E = 0\text{V}$
Emitter Cutoff Current	$I_{EBO}$	—	-50	nA	$V_{EB} = -3.0\text{V}, I_C = 0\text{V}$
<b>ON CHARACTERISTICS (Note 6)</b>					
DC Current Gain	$h_{FE}$	120 60	360 —	—	$I_C = -2.0\text{mA}, V_{CE} = -1.0\text{V}$ $I_C = -50\text{mA}, V_{CE} = -1.0\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	-0.40	V	$I_C = -50\text{mA}, I_B = -5.0\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	-0.95	V	$I_C = -50\text{mA}, I_B = -5.0\text{mA}$
<b>SMALL SIGNAL CHARACTERISTICS</b>					
Output Capacitance	$C_{obo}$	—	4.5	pF	$V_{CB} = -5.0\text{V}, f = 1.0\text{MHz}, I_E = 0$
Input Capacitance	$C_{ibo}$	—	10	pF	$V_{EB} = -0.5\text{V}, f = 1.0\text{MHz}, I_C = 0$
Small Signal Current Gain	$h_{fe}$	120	480	—	$V_{CE} = -1.0\text{V}, I_C = -2.0\text{mA},$ $f = 1.0\text{kHz}$
Current Gain-Bandwidth Product	$f_T$	250	—	MHz	$V_{CE} = -20\text{V}, I_C = -10\text{mA},$ $f = 100\text{MHz}$
Noise Figure	NF	—	4.0	dB	$V_{CE} = -5.0\text{V}, I_C = -100\mu\text{A},$ $R_S = 1.0\text{k}\Omega, f = 1.0\text{kHz}$

Notes: 6. Short duration pulse test used to minimize self-heating effect.

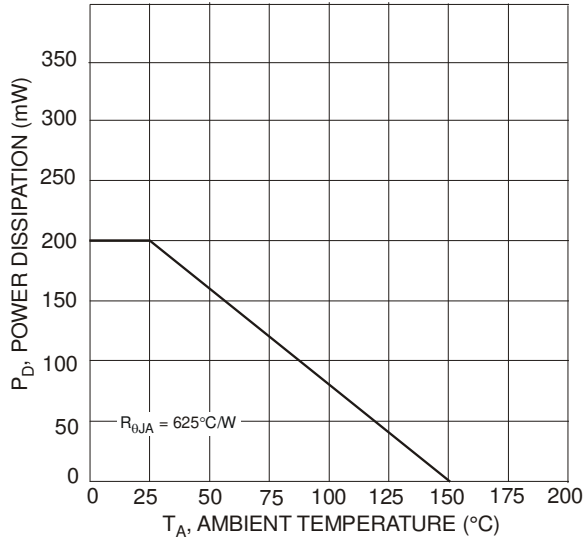


Fig. 1 Power Dissipation vs. Ambient Temperature (Total Device, Note 1)

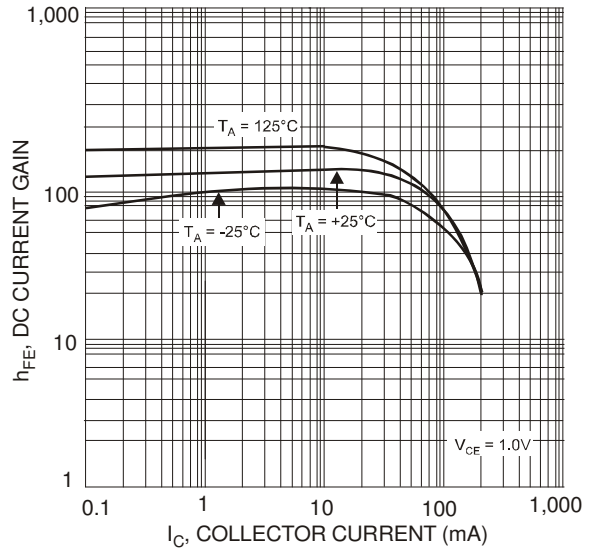


Fig. 2 Typical DC Current Gain vs. Collector Current (PNP-4126)

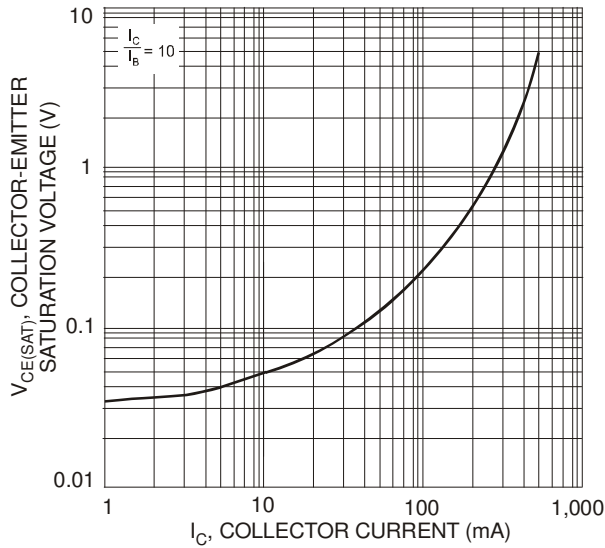


Fig. 3 Typical Collector-Emitter Saturation Voltage vs. Collector Current (PNP-4126)

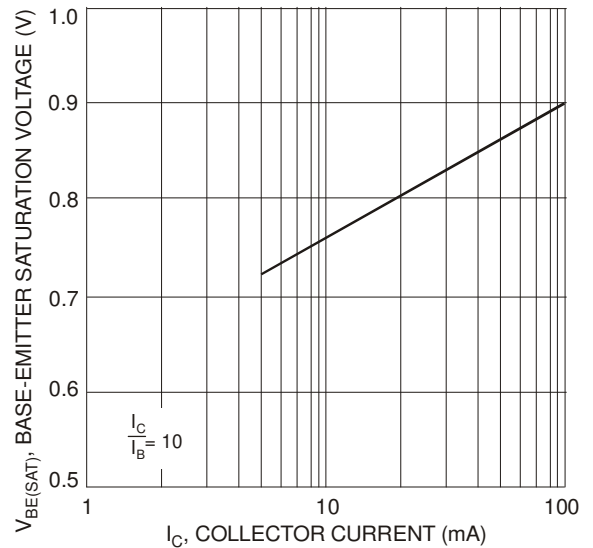


Fig. 4 Typical Base-Emitter Saturation Voltage vs. Collector Current (PNP-4126)

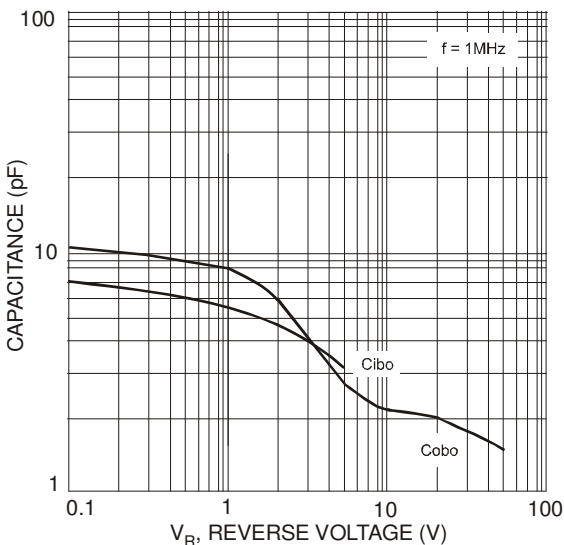


Fig. 5 Typical Capacitance Characteristics (PNP-4126)

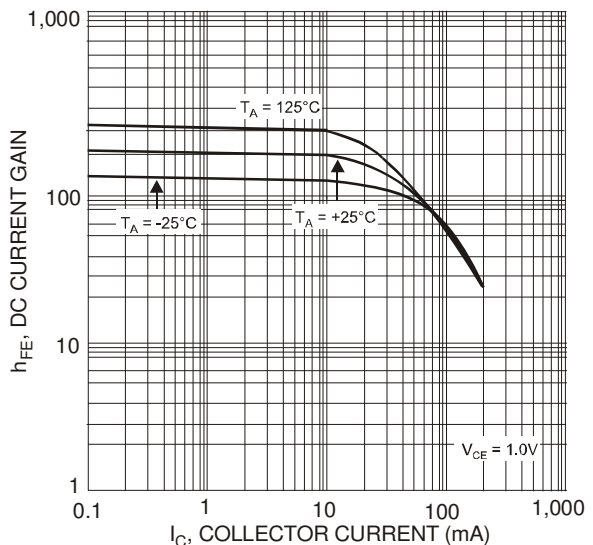


Fig. 6 Typical DC Current Gain vs. Collector Current (NPN-4124)

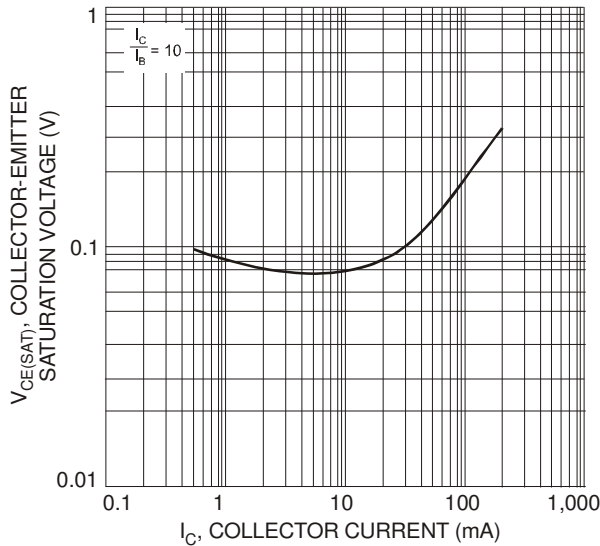


Fig. 7 Typical Collector-Emitter Saturation Voltage vs. Collector Current (NPN-4124)

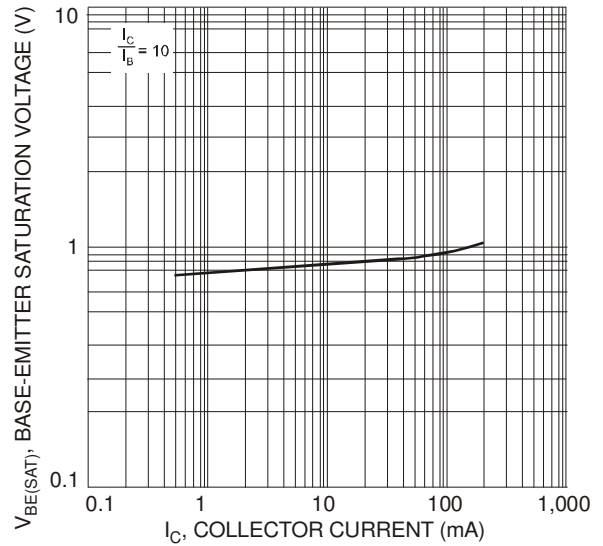


Fig. 8 Typical Base-Emitter Saturation Voltage vs. Collector Current (NPN-4124)

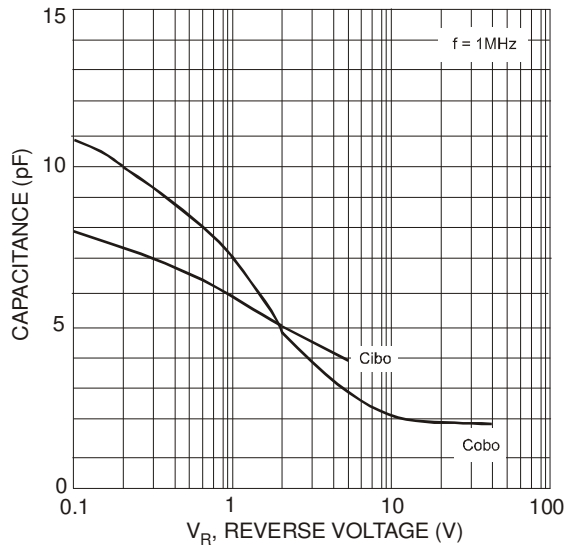


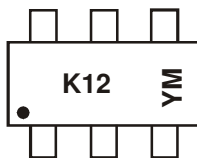
Fig. 9 Typical Capacitance Characteristics (NPN-4124)

**Ordering Information** (Note 7)

Part Number	Case	Packaging
MMDT4146-7-F	SOT-363	3000/Tape & Reel

Notes: 7. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

**Marking Information**

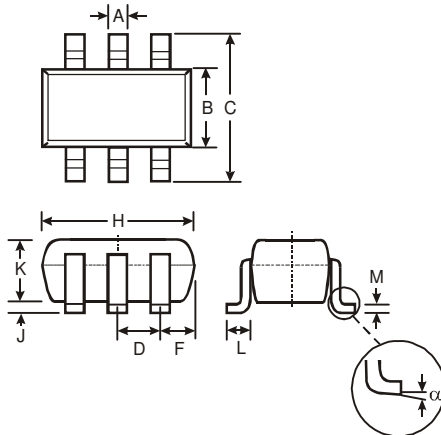


K12 = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: N = 2002)  
 M = Month (ex: 9 = September)

Date Code Key

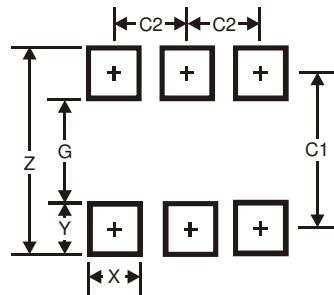
Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015
Code	J	K	L	M	N	P	R	S	T	U	V	W	X	Y	Z	A	B	C
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec						
Code	1	2	3	4	5	6	7	8	9	O	N	D						

**Package Outline Dimensions**



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Typ	
F	0.40	0.45
H	1.80	2.20
J	0	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.22
α	0°	8°
<b>All Dimensions in mm</b>		

**Suggested Pad Layout**



Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Y	0.6
C1	1.9
C2	0.65

**IMPORTANT NOTICE**

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. Diodes Incorporated does not assume any liability arising out of the application or use of any product described herein; neither does it convey any license under its patent rights, nor the rights of others. The user of products in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on our website, harmless against all damages.

**LIFE SUPPORT**

Diodes Incorporated products are not authorized for use as critical components in life support devices or systems without the expressed written approval of the President of Diodes Incorporated.